SWITCHMODE[™] Series **NPN Silicon Power** Transistor

This device is designed for high speed, high current, high power applications.

Features

- High DC Current Gain: h_{FE} min = 20 at I_C = 12 A
- Low V_{CE(sat)}, V_{CE(sat)} max = 0.6 V at I_C = 8 A
- Very Fast Switching Times: TF max = 0.4 μ s at I_C = 25 A
- These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO(SUS)}	200	Vdc
Collector-Base Voltage	V _{CBO}	250	Vdc
Emitter-Base Voltage	V _{EBO}	7	Vdc
Collector-Emitter Voltage (V _{BE} = -1.5 V)	V _{CEX}	250	Vdc
Collector–Emitter Voltage (R_{BE} = 100 Ω)	V _{CER}	240	Vdc
Collector–Current – Continuous – Peak (PW ≤ 10 ms)	I _C I _{CM}	40 50	Adc Apk
Base-Current Continuous	Ι _Β	8	Adc
Total Device Dissipation @ $T_C = 25^{\circ}C$	PD	250	W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to 200	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θ_{JC}	0.7	°C/W

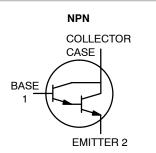
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

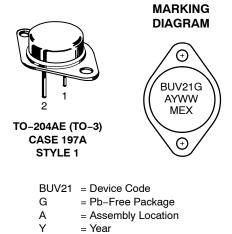


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40 AMPERES NPN SILICON POWER METAL TRANSISTOR 200 VOLTS - 250 WATTS





Y	= Year
WW	= Work Week

MEX	= Country of Origin

ORDERING INFORMATION

Device	Package	Shipping
BUV21G	TO-204 (Pb-Free)	100 Units / Tray

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS

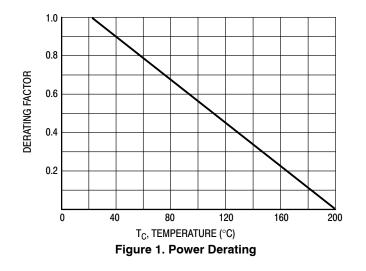
	Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS (Note	• 1)				
Collector–Emitter Sustaining Vo $(I_C = 200 \text{ mA}, I_B = 0, L = 25 \text{ m})$	5	V _{CEO(sus)}	200		Vdc
	$T_{C} = 25^{\circ}C$ unless otherwise noted)	I _{CEX}		3.0 12.0	mAdc
Collector-Emitter Cutoff Curren (V _{CE} = 160 V)	t	I _{CEO}		3.0	mAdc
Emitter-Base Reverse Voltage (I _E = 50 mA)		V _{EBO}	7		V
Emitter–Cutoff Current (V _{EB} = 5 V)		I _{EBO}		1.0	mAdc
SECOND BREAKDOWN		L	<u> </u>	•	
Second Breakdown Collector C (V_{CE} = 20 V, t = 1 s) (V_{CE} = 140 V, t = 1 s)	urrent with base forward biased	I _{S/b}	12 0.15		Adc
ON CHARACTERISTICS (Note	1)				
DC Current Gain (I _C = 12 A, V _{CE} = 2 V) (I _C = 25 A, V _{CE} = 4 V)		h _{FE}	20 10	60	
$ Collector-Emitter Saturation Vo \\ (I_C = 12 \text{ A}, I_B = 1.2 \text{ A}) \\ (I_C = 25 \text{ A}, I_B = 3 \text{ A}) $	Itage	V _{CE(sat)}		0.6 1.5	Vdc
Base–Emitter Saturation Voltag $(I_C = 25 \text{ A}, I_B = 3 \text{ A})$	e	V _{BE(sat)}		1.5	Vdc
DYNAMIC CHARACTERISTICS			,	•	•
Current Gain – Bandwidth Prod $(V_{CE} = 15 \text{ V}, I_C = 2 \text{ A}, f = 4 \text{ M})$		f _T	8.0		MHz
SWITCHING CHARACTERISTIC	CS (Resistive Load)		.,	•	•
Turn-on Time		t _{on}		1.0	μs
Storage Time	$(I_{C} = 25 \text{ A}, I_{B1} = I_{B2} = 3 \text{ A}, V_{CC} = 100 \text{ V}, R_{C} = 4 \Omega)$	t _s		1.8	1
Fall Time		+.		0.4	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%.

0.4

t_f

Fall Time



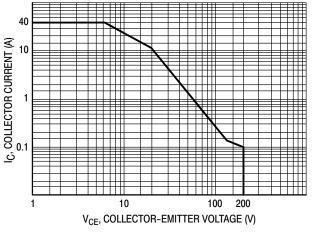


Figure 2. Active Region Safe Operating Area

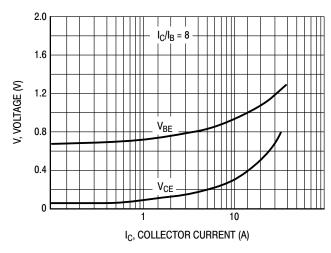


Figure 3. "On" Voltages

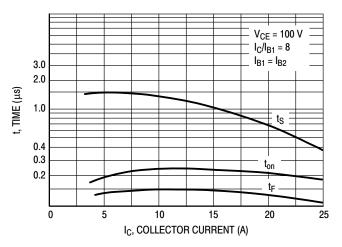


Figure 5. Resistive Switching Performance

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_C = 25^{\circ}C$, $T_{J(pk)}$ is variable depending on power level. Second breakdown limitations do not derate the same as thermal limitations.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

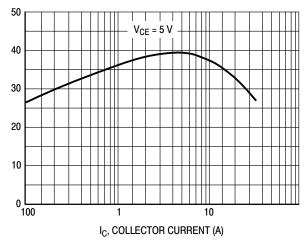
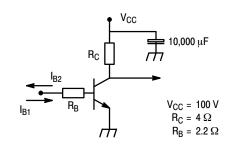


Figure 4. DC Current Gain

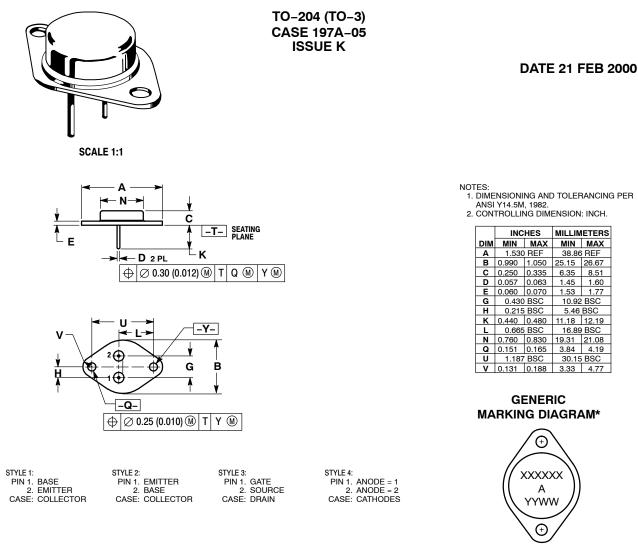


R_C – R_B: Non inductive resistances

Figure 6. Switching Times Test Circuit

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XXXXX = Specific Device Code

A = Assembly Locationa

YY = Year

WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking.

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